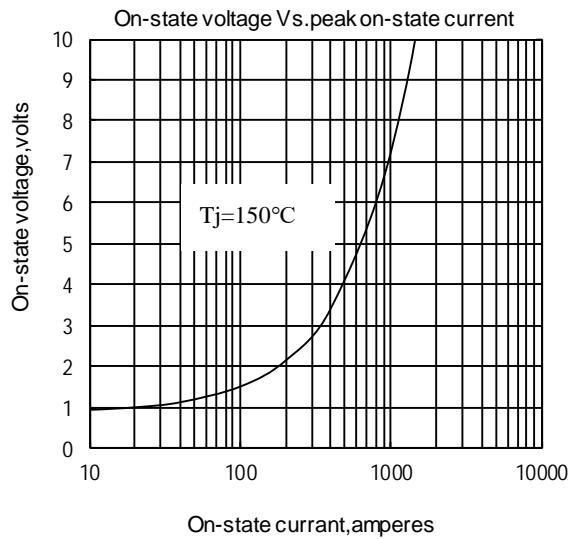
**Features:**

- Planar passivated chip
- Long-term stability
- Non-isolated type

**Typical Applications:**

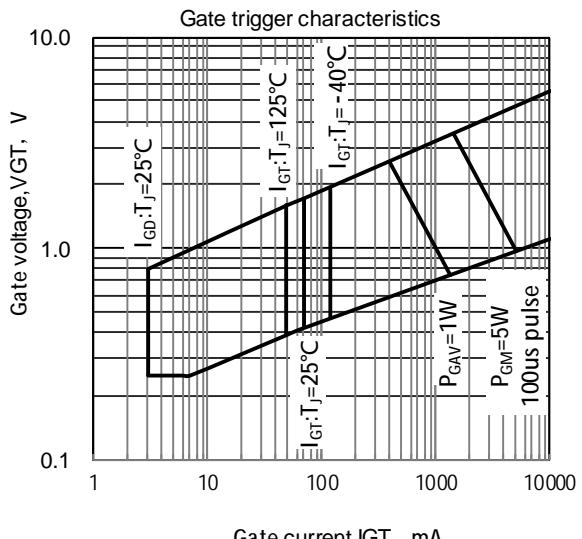
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T <sub>j</sub> (°C)	VALUE			UNIT
				Min	Type	Max	
I <sub>T(RMS)</sub>	RMS on-state current	180° half sine wave 50Hz	T <sub>c</sub> =115°C	150		75	A
V <sub>DRM</sub> V <sub>RRM</sub>	Repetitive peak off-state voltage Repetitive peak reverse voltage	tp=10ms		25		1600	V
I <sub>DRM</sub> I <sub>RRM</sub>	Repetitive peak off-state current Repetitive peak reverse current	at V <sub>DRM</sub> /V <sub>RRM</sub>	25			50	µA
			150			10	mA
I <sub>TSM</sub>	Surge on-state current	10ms half sine wave	25			600	A
I <sup>2</sup> t	I <sup>2</sup> t value for fusing		25			1800	A <sup>2</sup> s
V <sub>TM</sub>	Peak on-state voltage	I <sub>TM</sub> =100A	25			1.70	V
di/dt	Critical rate of rise of on-state current	I <sub>G</sub> =2*I <sub>GT</sub>	25			150	A/µs
dv/dt	Critical rate of rise of off-state voltage	V <sub>D</sub> =2/3V <sub>DRM</sub> Gate Open	150			1000	V/µs
I <sub>L</sub>	Latching current	I <sub>G</sub> =1.2 I <sub>GT</sub>	25			150	mA
I <sub>GT</sub>	Gate trigger current	V <sub>D</sub> =12V R <sub>L</sub> =33Ω	25	30		70	mA
V <sub>GT</sub>	Gate trigger voltage					1.5	V
I <sub>H</sub>	Holding current	I <sub>T</sub> =1.0A	25			120	mA
V <sub>GD</sub>	Non-trigger gate voltage	V <sub>D</sub> =V <sub>DRM</sub> R <sub>L</sub> =3.3kΩ	150			0.25	V
I <sub>GM</sub>	Peak gate current					4	A
P <sub>G(AV)</sub>	Average gate power dissipation					1	W
P <sub>GM</sub>	Peak gate power					5	W
R <sub>th(j-c)</sub>	Thermal resistance Junction to case				0.3		°C/W
T <sub>stg</sub>	Storage junction temperature range			-40		150	°C
T <sub>vj</sub>	Virtual junction temperature			-40		150	°C
T <sub>OP</sub>	Operation temperature			-40		150	°C
Outline	TO-247H						



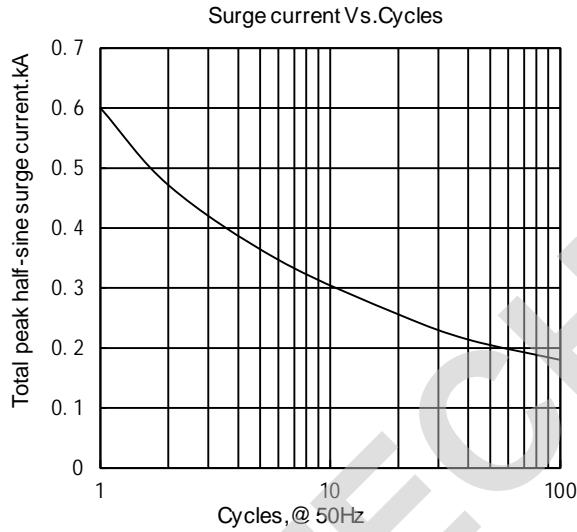
On-state currant,amperes

Fig1



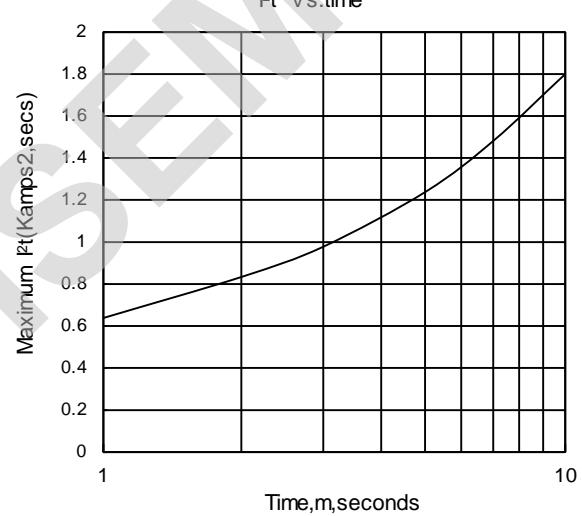
Gate current,IGT, mA

Fig2



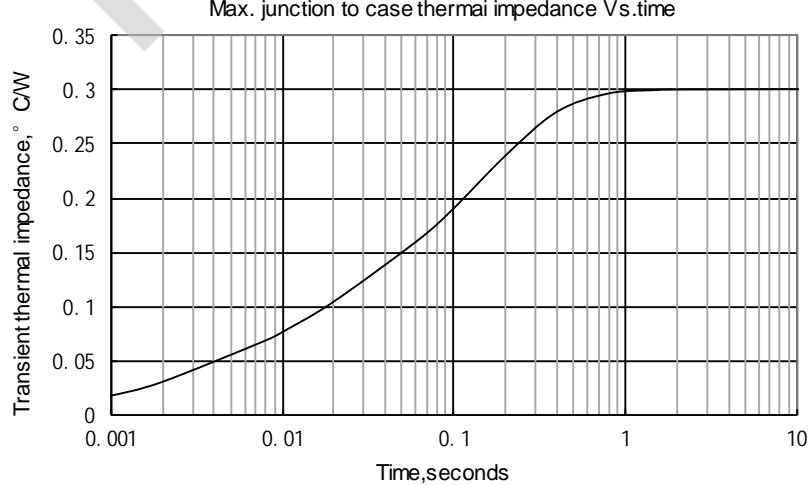
Cycles,@ 50Hz

Fig3



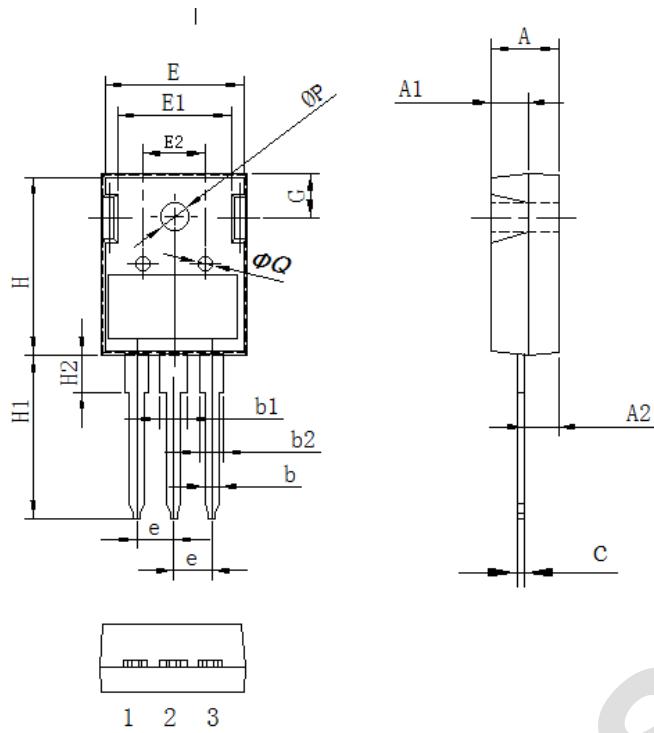
Time,m,seconds

Fig4

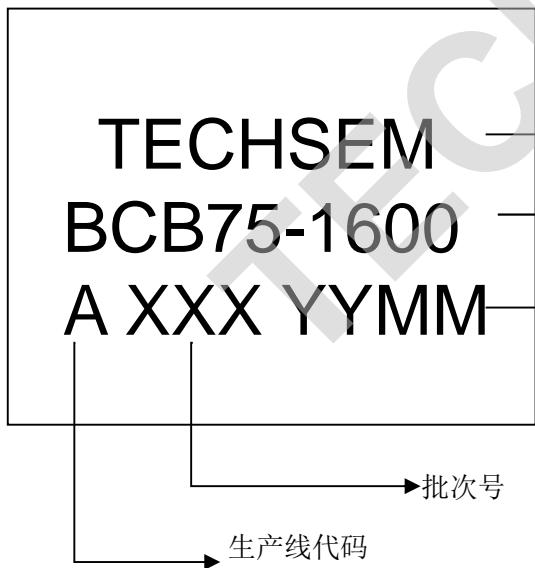


Time,seconds

Fig5

**Outline:****TO-247H PACKAGE**

Symbol	单位 mm		
	Min	Nom	Max
A	4.80	5.00	5.20
A1	2.80	3.00	3.20
A2	2.20	2.40	2.60
b	1.05	1.20	1.35
b1	2.80	3.00	3.20
b2	1.80	2.00	2.20
c	0.50	0.60	0.70
e	5.35	5.45	5.75
E	15.6	15.8	16.0
E1	12.3	12.5	12.7
E2	6.00	6.20	6.40
H	20.8	21.0	21.2
H1	19.5	20.0	20.5
H2	3.70	4.00	4.30
G	5.70	5.90	6.10
ΦP	3.30	3.50	3.70
ΦQ	2.30	2.50	2.70

**Code Designation:**

→ 产品商标: 湖北台基半导体股份有限公司

→ 产品型号

→ 产品出厂日期: YY 表示出厂年份, MM 表示第 MM 周

→ 批次号

→ 生产线代码

**Product Nomenclature:**

Type	$I_{T(RMS)}$	$V_{DRM}, V_{RRM}$	$I_{TSM}$	$T_{jmax}$	Marking	Outline
<b>BCB75-1600</b>	<b>75A(<math>T_c=115^\circ C</math>)</b>	<b>1600V</b>	<b>600A</b>	<b>150°C</b>	<b>BCB75-1600</b>	<b>TO-247H</b>